## ELECTRONIC SUPPLEMENTARY INFORMATION

## Improving the thermoelectric properties of half-Heusler TiNiSn through inclusion of a secondary full-Heusler phase: Microwave preparation and Spark Plasma Sintering of $TiNi_{1+x}Sn$

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## Analytical conditions of microprobe analysis

Ti K $\alpha$ , Ni K $\alpha$ , and Sn L $\alpha$  X-ray intensities were measured using LPET, LLIF, and LPET analyzing crystals. X-ray intensity maps were collected using 15 keV accelerating voltage with 100 nA of beam current. An area of 125×125 µm was traversed using continuous stage translation to create a 256×256 pixel map with a dwell time of 125 ms per pixel. Quantitative analysis was conducted at 15 keV accelerating voltage and 10 nA beam current. Ti K $\alpha$ , Ni K $\alpha$ , and Sn L $\alpha$  intensities were measured on-peak for 20 seconds and 10 seconds off-peak either side of the peak to create a linear background interpolation.



Figure S1. SEM images of as-prepared TiNiSn, TiNi1.06Sn, and TiNi1.15Sn

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**Figure S2.** Microprobe images of  $TiNi_{1+x}Sn$  with x = 0, 0.04, 0.1, and 0.15.